

# PIN Diode IV Characteristics, Transient Analysis & Application

## Electronic Devices and Characterization Experiment 2

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# Background Theory

- PIN diode has a wide, un-doped intrinsic semiconductor region between 'P' and 'N' regions. The P-type and N-type regions are typically heavily doped.



- PIN diode obeys the standard diode equation for low-frequency signals. At higher frequencies, the diode looks like an almost perfect resistor.
- Under zero- or reverse-bias, a PIN diode has a low capacitance. The low capacitance will not pass much of an RF signal. Under a forward bias, a PIN diode will have a low RF resistance, making it a good conductor of RF. Consequently, the PIN diode makes a good RF switch.

# Aim of the experiment

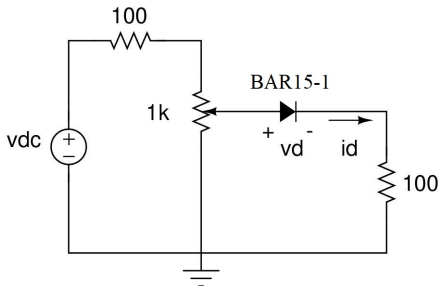
- To find forward voltage, reverse saturation current and ideality factor of the given PIN diode (Infineon BAR 15-1) and compare with normal PN junction Diode (1N4007).
- To find reverse recovery time of the given PIN diode at various frequencies and compare with the reverse recovery time of normal PN junction Diode.
- To observe how the PIN diode works as an RF switch at different DC bias voltages.

# Components required

- PIN diode Infineon BAR 15-1, PN junction diode 1N4007.
- Resistors -  $500\Omega$  ( $\times 2$ ),  $50\Omega$ ,  $1k\Omega$
- Potentiometer -  $1k\Omega$
- Capacitors -  $100nF$  ( $\times 2$ )
- Breadboard, connecting wires
- Multi-meters, variable power supply, signal generator and oscilloscope

# Experiment-Part 1

- 1 Make the connections as per the circuit diagram. Notice the role of the  $1k\Omega$  pot, that can be used to vary the voltage to be applied to the diode.
- 2 Vary  $V_D$  in suitably small steps (from 0 V to 1 V only), and measure and tabulate  $I_D$  and  $V_D$  for each step.



**Figure:** Circuit to measure I/V characteristics of a semiconductor diode

You are advised to simultaneously plot I-V in the lab, to quickly identify if the measurement is as expected.

## Experiment-Part 2

Apply square wave of different frequencies (10 *KHz*, 100 *kHz*, 1 *MHz*, 3 *MHz*) to the given circuit (for both PIN diode and PN diode) and note down the reverse recovery times.

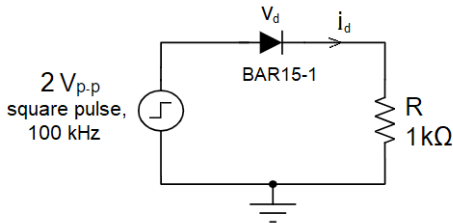
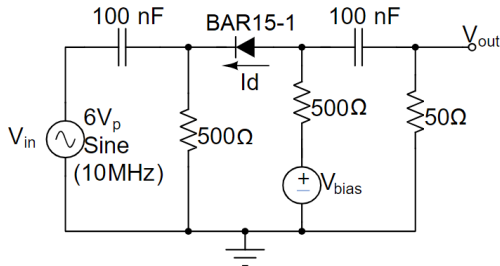


Figure: Circuit to measure reverse recovery time

Which diode has the potential of passing major portion of the input signal to the output at 3 *MHz*?

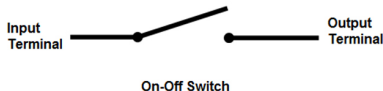
# Experiment-Part 3

Make the circuit as shown and find sinusoidal output voltage and diode DC current for different DC bias voltages ( $-5\text{ V}$ ,  $0\text{ V}$ ,  $1\text{ V}$ ,  $3\text{ V}$ ,  $5\text{ V}$ ).



**Figure:** Circuit to characterize PIN diode as RF switch

Repeat the experiment using regular PN junction diode and note down the results. Relate the PIN diode circuit with an SPST switch.



# Documenting Results

Table format for reverse recovery time comparison (part 2).

Frequency	RRT of PIN	RRT of PN
10 kHz		
100 kHz		
1 MHz		
3 MHz		

Table format for RF switch (part 3).

$V_{bias}$	$I_D$	$V_{out}$
-5V		
0V		
1V		
3V		
5V		



# BAR15-1 Device

The Infineon BAR15-1 PIN Diode has a common cathode structure.

